

isc Silicon NPN Power Transistors

2SD5071

DESCRIPTION

- · High Breakdown Voltage-
- : V_{CBO}= 1500V (Min)
- · High Switching Speed
- · High Reliability
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

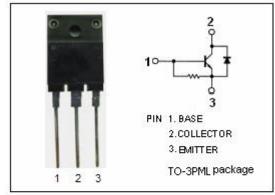


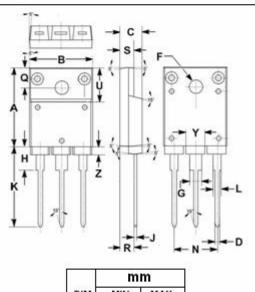
APPLICATIONS

 Designed for use in horizontal deflection circuits of colour TV receivers.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------------|
| V _{CBO} | Collector-Base Voltage | 1500 | V |
| Vceo | Collector-Emitter Voltage | 800 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| Ic | Collector Current-Continuous | 3.5 | А |
| Ісм | Collector Current-Peak | 10 | Α |
| Pc | Collector Power Dissipation @T _c =25℃ | 50 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ |





| | mm | | |
|-----|-------|-------|--|
| DIM | MIN | MAX | |
| Α | 19.90 | 20.10 | |
| В | 15.75 | 16.10 | |
| С | 5.50 | 5.70 | |
| D | 0.90 | 1.10 | |
| Ŧ | 3.30 | 3.50 | |
| G | 2.90 | 3.20 | |
| Н | 5.90 | 6.10 | |
| J | 0.595 | 0.70 | |
| K | 21.10 | 22.50 | |
| L | 1.90 | 2.25 | |
| N | 10.80 | 11.00 | |
| 0 | 4.90 | 5.10 | |
| R | 3.75 | 3.95 | |
| S | 3.20 | 3.60 | |
| U | 9.90 | 10.10 | |
| Y | 4.20 | 4.90 | |
| Z | 1.90 | 2.10 | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|-----|-----|------|
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 2.5A; I _B = 0.8A | | | 8.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 2.5A ;I _B = 0.8A | | | 1.5 | V |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 4V; I _C =0 | 40 | | 200 | mA |
| I _{CBO} | Collector-Base Cutoff Current | V _{CB} =800V; I _E = 0 | | | 10 | uA |
| h _{FE} | DC Current Gain | I _C = 0.5A; V _{CE} = 5V | 8 | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = 0.5A; V _{CE} = 10V | | 3 | | MHz |
| V _{ECF} | C-E Diode Forward Voltage | I _F = 3.5A | | | 2.0 | V |
| tf | Fall Time | Ic= 3A, I _{B1} = 0.8A; I _{B2} = -1.6A R _L = 66.7 Ω; V _{CC} = 200V | | | 0.4 | us |

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